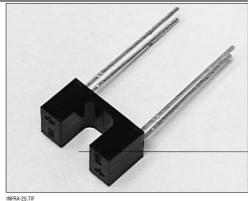
### **Transmissive Sensor**

#### **FEATURES**

- Choice of phototransistor or photodarlington output
- Compact package size
- · Dust protective housing
- 0.060 in.(1.52 mm)dia. detector aperture
- 0.200 in.(5.08 mm) slot width



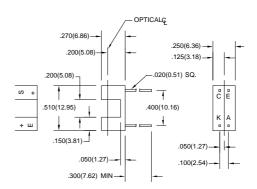
#### DESCRIPTION

The HOA1882 series consists of an infrared emitting diode facing an NPN silicon phototransistor (HOA1882-011, -012) or photodarlington (HOA1882-013) encased in a black IR transmissive thermoplastic housing. Detector switching takes place whenever an opaque object passes through the slot between emitter and detector. The HOA1882 series employs an IR transmissive housing which features smooth optical faces without external aperture openings; this feature is desirable when aperture blockage from airborne contaminants is a possibility. The HOA1882 series employs plastic molded components. For additional component information see SEP8506/8706, SDP8406, and SDP8106.

Housing material is IR transmissive polysulfone. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

#### OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)



DIM\_053.cdr



### **Transmissive Sensor**

#### ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I <sub>F</sub> =20 mA
Reverse Leakage Current	l <sub>R</sub>			10	μΑ	V <sub>R</sub> =3 V
DETECTOR						
Collector-Emitter Breakdown Voltage	V <sub>(BR)</sub> ceo				V	Ic=100 μA
HOA1882-011, -012		30				
HOA1882-013		15				
Emitter-Collector Breakdown Voltage	V <sub>(BR)ECO</sub>	5.0			V	I <sub>E</sub> =100 μA
Collector Dark Current	ICEO				nA	V <sub>CE</sub> =10 V
HOA1882-011, -012				100		l <sub>F</sub> =0
HOA1882-013				250		
COUPLED CHARACTERISTICS						
On-State Collector Current	Ic(on)				mA	V <sub>CE</sub> =5 V
HOA1882-011		0.3				I <sub>F</sub> =20 mA
HOA1882-012		1.8				
HOA1882-013		4.0				
Collector-Emitter Saturation Voltage	VCE(SAT)				V	I <sub>F</sub> =20 mA
HOA1882-011				0.4		Ic=40 μA
HOA1882-012				0.4		Ic=230 μA
HOA1882-013				1.1		Ic=500 μA
Rise And Fall Time	t <sub>r</sub> , t <sub>f</sub>				μs	Vcc=5 V, lc=1 mA
HOA1882-011, -012			15			R <sub>L</sub> =1000 Ω
HOA1882-013			75			R <sub>L</sub> =100 Ω

#### **ABSOLUTE MAXIMUM RATINGS**

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C

Storage Temperature Range -40°C to 85°C

Soldering Temperature (5 sec) 240°C

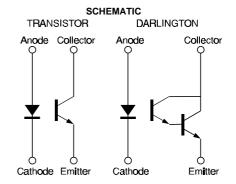
IR EMITTER

Power Dissipation 100 mW <sup>(1)</sup>
Reverse Voltage 3 V
Continuous Forward Current 50 mA

DETECTORTRANS.DARLINGTONCollector-Emitter Voltage30 V15 VEmitter-Collector Voltage5 V5 VPower Dissipation100 mW (¹)100 mW (¹)

Notes

1. Derate linearly at 0.78 mW/°C above 25°C.

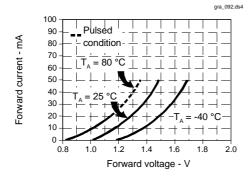


Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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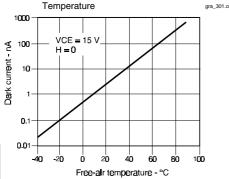
### **Transmissive Sensor**

Fig. 1 IRED Forward Bias Characteristics



Non-Saturated Switching Time vs Load Resistance 1000 ▤◾▦▦ Response time - µs 100 Photodarlington = | | Phototransistor ŦI#I# 10 100 1000 10000

Fig. 3 Dark Current vs



Collector Current vs Fig. 4 Ambient Temperature gra\_095.ds4 Normalized collector current 1.0 0.6 0.4 0.2 0.0 75 -50 Ó 25 50 100

Free-air temperature - °C

Load resistance - Ohms

All Performance Curves Show Typical Values

**Transmissive Sensor** 

